



# Accuracy and Robustness of FDTD Simulation of Devices Characterized by Measured S-Parameters

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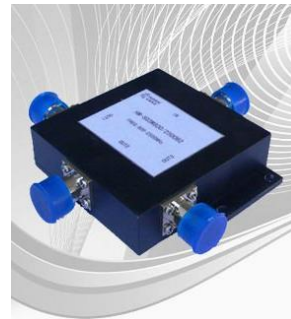
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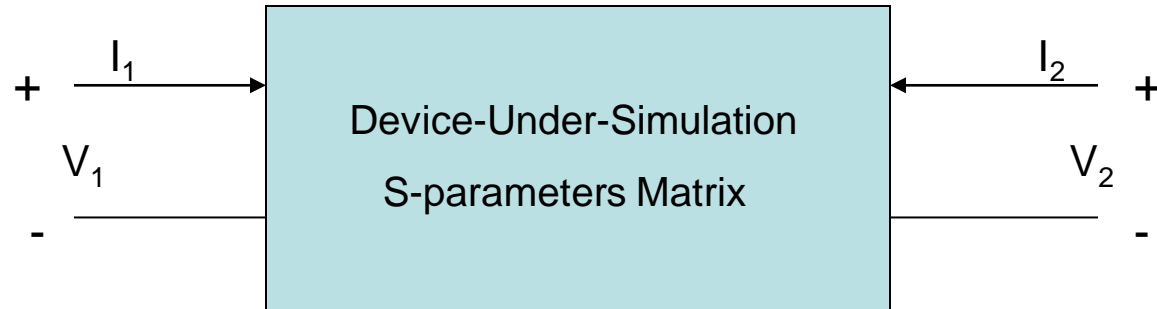
# Motivation of This Work

Simulate passive and active circuits characterized by simulated and measured S-parameters together with other geometries in FDTD.

- Filters
- Power Dividers
- Amplifiers
- Circulators
- RF Systems
- Inductors
- Capacitors



# Convolution Method



$$\begin{bmatrix} S_{11}(s) & S_{21}(s) \\ S_{21}(s) & S_{22}(s) \end{bmatrix} \Rightarrow \begin{bmatrix} Y_{11}(s) & Y_{21}(s) \\ Y_{12}(s) & Y_{22}(s) \end{bmatrix} \Rightarrow \begin{bmatrix} Y_{11}(t) & Y_{21}(t) \\ Y_{12}(t) & Y_{22}(t) \end{bmatrix}$$

$$\begin{bmatrix} I_1(s) \\ I_2(s) \end{bmatrix} = \begin{bmatrix} Y_{11}(s) & Y_{12}(s) \\ Y_{21}(s) & Y_{22}(s) \end{bmatrix} \begin{bmatrix} V_1(s) \\ V_2(s) \end{bmatrix} \Rightarrow \begin{bmatrix} I_1(t) \\ I_2(t) \end{bmatrix} = \begin{bmatrix} Y_{11}(t) \otimes V_1(t) + Y_{12}(t) \otimes V_2(t) \\ Y_{21}(t) \otimes V_1(t) + Y_{22}(t) \otimes V_2(t) \end{bmatrix}$$

Ye and Drewniak, *IEEE Trans. Electromagnetic Compatibility*, vol.44, no.1, pp. 175–181, 2002.

Luo and Chen, *IEEE Trans. Microwave Theory Tech.*, vol. 53, no. 3, pp. 969–976, Mar. 2005.

# Inverse Laplace Transform

$$Y(s) \approx \sum_{i=1}^M \frac{r_i}{s - p_i} + \alpha \quad \longrightarrow \quad y(t) \approx \alpha \delta(t) + u(t) \sum_{i=1}^M r_i e^{p_i t}$$

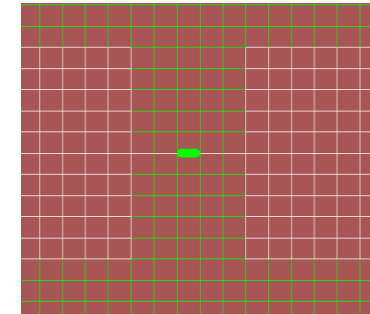
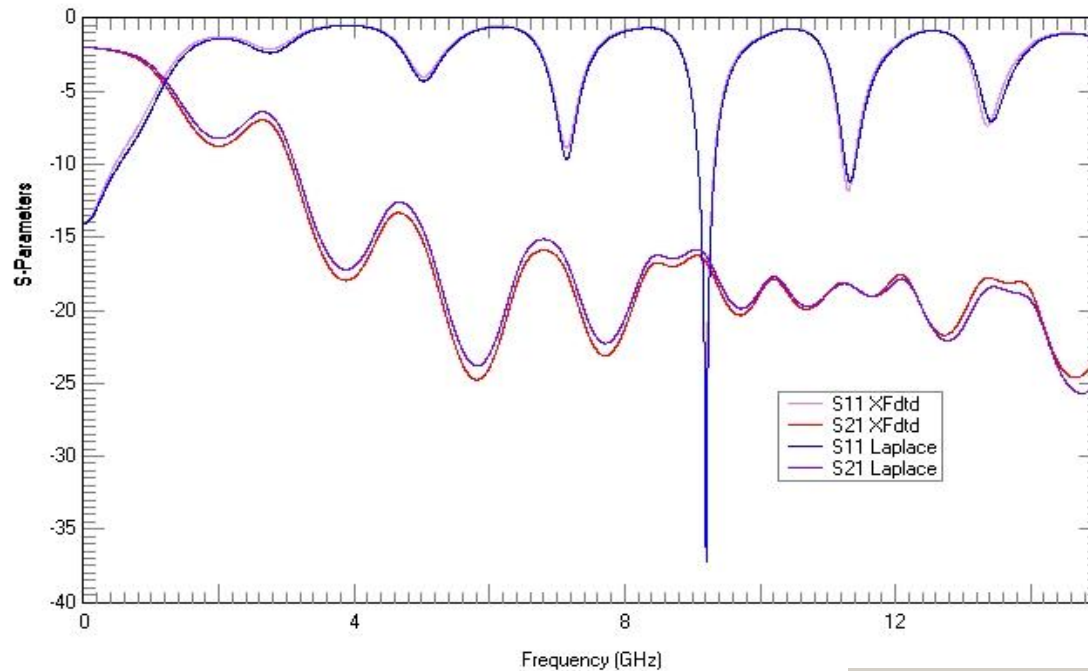
$$i(t)_{t=k\Delta t} = [y(t) \otimes v(t)]$$

$$i(t)_{t=k\Delta t} = \alpha v(t)_{t=\Delta t} + \sum_{i=1}^M r_i \psi_i(t)_{t=k\Delta t}$$

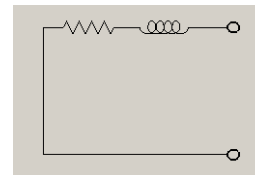
$$\psi_i(t)_{t=k\Delta t} = e^{p_i \Delta t} \psi_i(t)_{t=(k-1)\Delta t} + \Delta t / 2 \left[ e^{p_i \Delta t} v(t)_{t=(k-1)\Delta t} + v(t)_{t=k\Delta t} \right]$$

Luo and Chen, *IEEE Transactions on Circuits and Systems—I: regular papers*, vol.52, no.6, pp.1205-1210, 2005.

# FDTD vs. Inverse Laplace Transform



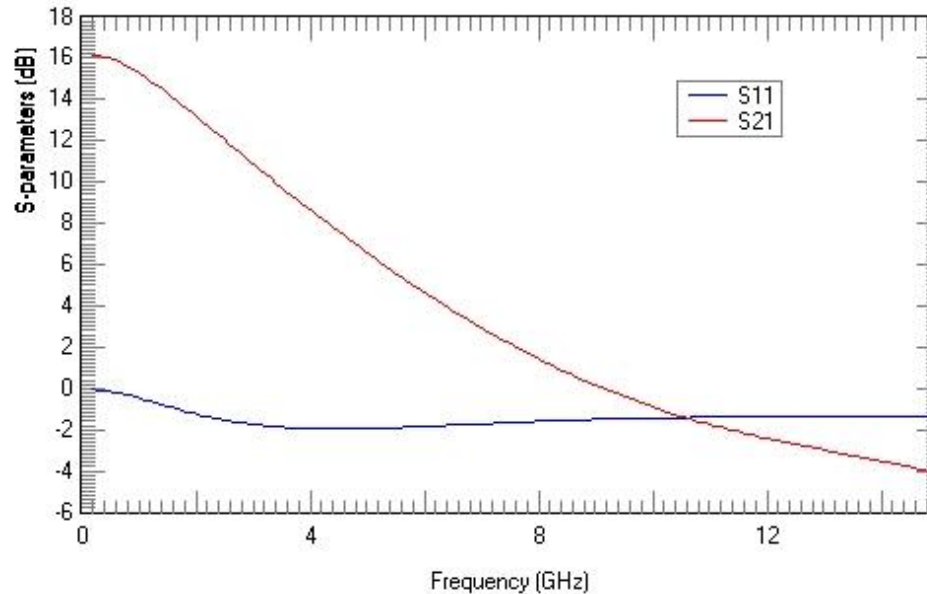
$$Y(s) = \frac{1/L}{s - (-R/L)}$$



A series RL circuit (R=25 Ohm, L=10 nH) simulated by Remcom's XFDTD<sup>®</sup> and the inverse Laplace transform.

# Bilinear-Transform

$$Y_{pq}(s) = \frac{\sum_{m=0}^{M_{pq}} a_m^{(p,q)} s^m}{\sum_{n=0}^{N_{p,q}} b_n^{(p,q)} s^n} + s = \frac{2}{\Delta t} \frac{1 - z^{-1}}{1 + z^{-1}} \longrightarrow Y_{pq}(z) = \frac{\sum_{m=0}^{M_{pq}} c_m^{(p,q)} z^{-m}}{1 + \sum_{n=0}^{N_{p,q}} d_n^{(p,q)} z^{-n}}$$



González et al, *IEEE Microwave and Wireless Components Lett.*, vol.17, no.7, pp.477-479, 2007.

Simulated S-parameters of a MESFET characterized by analytical Y-parameters.



# Passivity Enhancement Method

- Transient circuit simulators: admittance representations in form of rational transfer functions.
- Measured or calculated frequency domain responses are band limited, error contaminated and not in the appropriate rational form.
- A reduced order rational model has to be causal, stable, passive and accurate.
- The passivity enhancement method was proposed using an inverse eigenvalue method.

Saunders and Steer, *IEEE Trans. Microwave Theory Tech.*, vol.60, no.1, pp.8-20, 2012.

# Poles/Residues of a Bandpass Filter

## A SAW filter for GPS applications: 14 complex poles and residues

### $Y_{11}$ Residues

(34070.584551123633,-53119.371112613575)  
(1460094.778391400800,-109000.419673486210)  
(1155778.530517811400,-14927.811108331025)  
(373186.902657350180,38834.913235098669)  
(39805.171980597923,-4659.906070365948)  
(-71913.182212009619,845344.246937821270)  
(1210318408.436479100000,1919087340.209662200000)

### $Y_{21}$ Residues

(-176963.948006825550,-35337.290654441298)  
(1091876.690182048400,-109139.966116357430)  
(-1177086.810548629100,54361.396008882140)  
(383378.830882090490,46021.439147500911)  
(-59336.084264568235,6589.844513568966)  
(-313508.010614982460,-95471.447472298940)  
(86903227.091137365000,-100182463.143305690000)

### $Y_{12}$ Residues

(-176963.948006825550,-35337.290654441298)  
(1091876.690182048400,-109139.966116357430)  
(-1177086.810548629100,54361.396008882140)  
(383378.830882090490,46021.439147500911)  
(-59336.084264568235,6589.844513568966)  
(-313508.010614982460,-95471.447472298940)  
(86903227.091137365000,-100182463.143305690000)

### $Y_{22}$ Residues

(885013.404124003020,-312160.416136991350)  
(847677.403772644820,-16113.604622687069)  
(1172943.432175491700,-24150.176920717440)  
(466611.182901630700,24437.542630346048)  
(75622.559246770485,-6500.701101628966)  
(290699.236360470760,1276739.963624418500)  
(970627068.057553170000,1968655525.232881300000)

### Poles

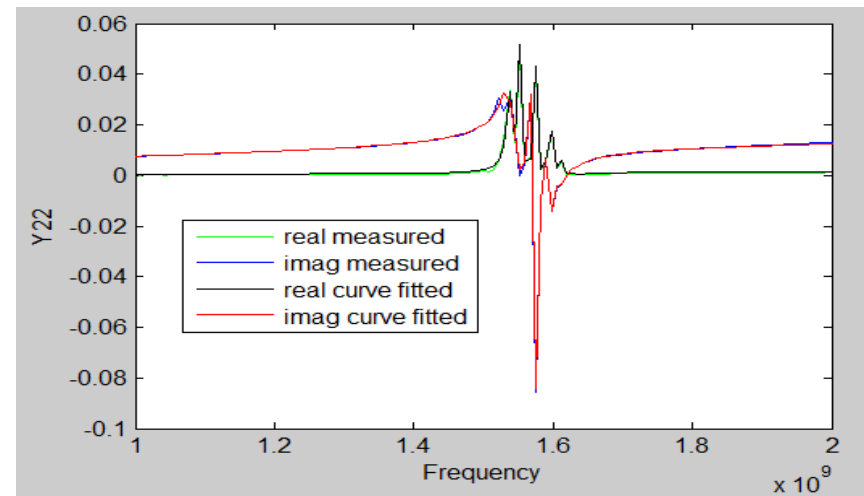
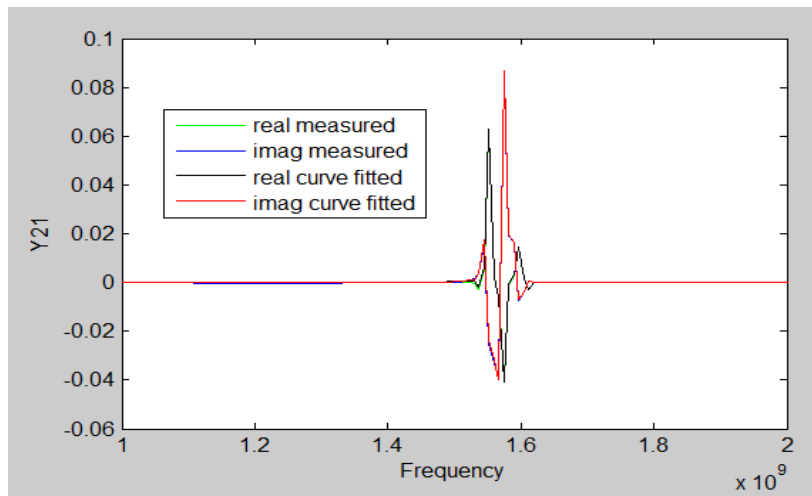
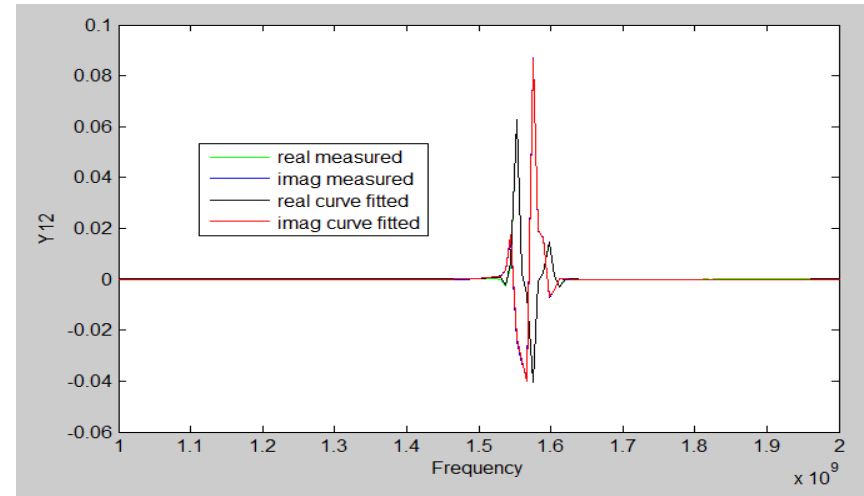
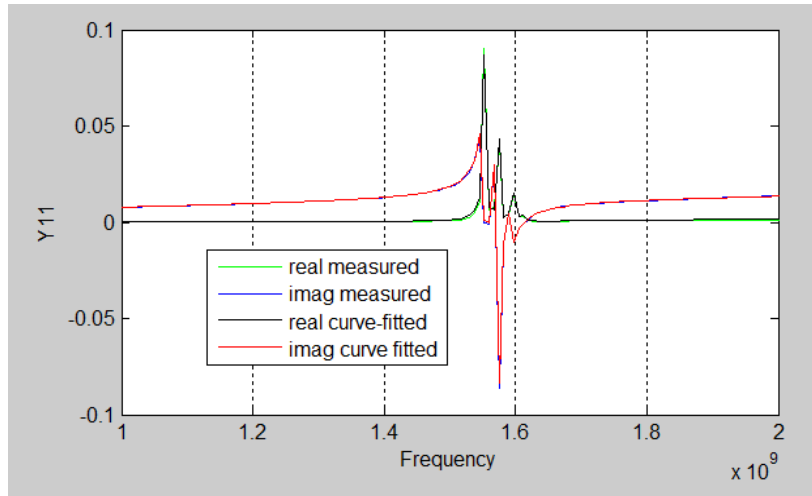
(-27893371.461747594000,9672195057.513483000000)  
(-16202050.648703106000,9751617287.788698200000)  
(-5305167.867902691500,9884716723.278949700000)  
(-16053548.027104480000,10022541470.749012000000)  
(-13704553.940730477000,10125697554.577724000000)  
(-1035163298.384340900000,10591442623.479601000000)  
(-24864884250.049561000000,57867968741.893501000000)

### $\alpha$

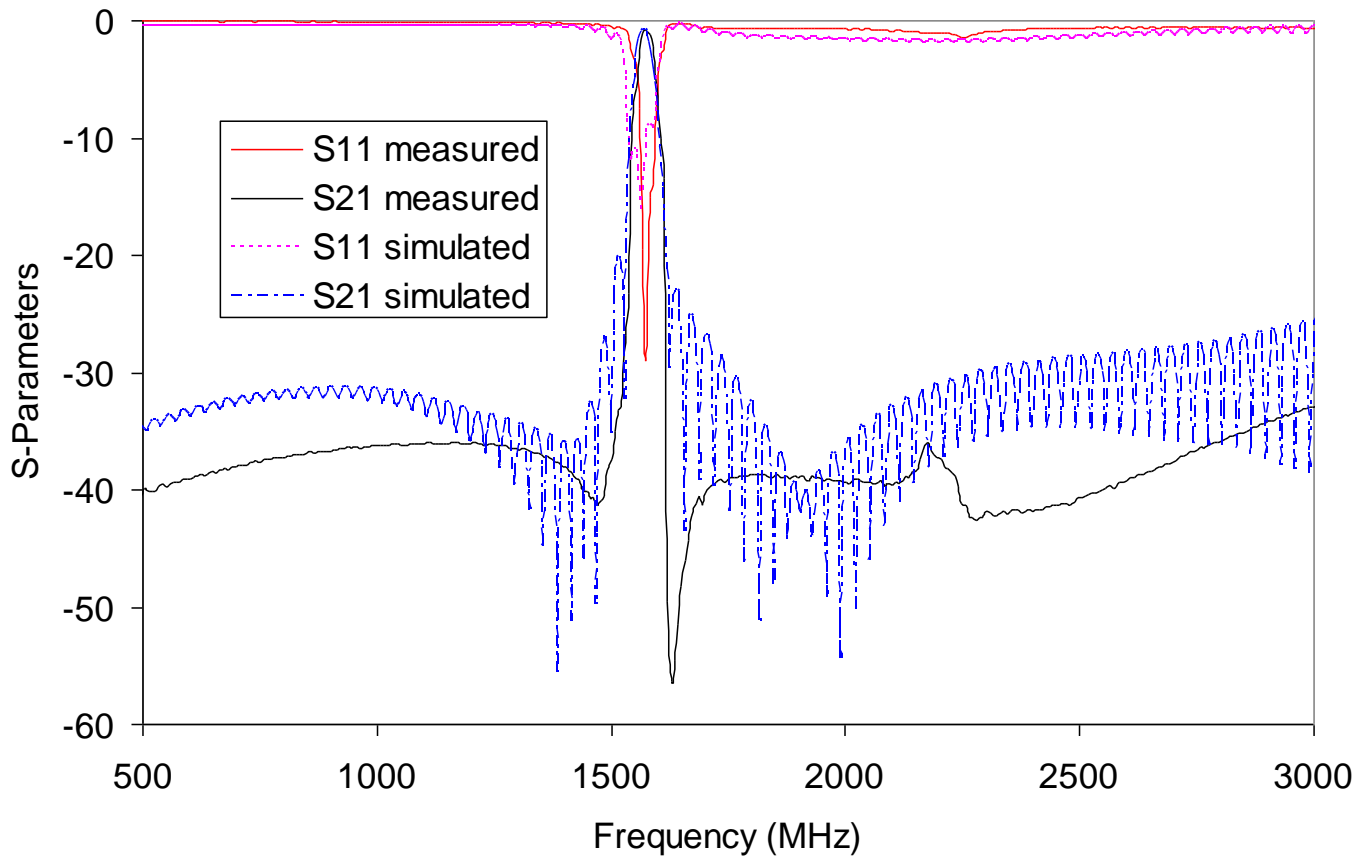
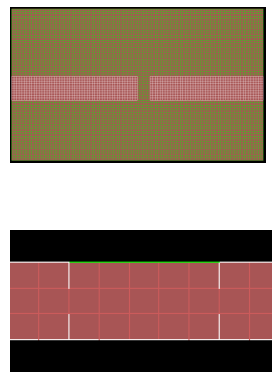
$Y_{11}$  0.041275638722673  
 $Y_{12}$  -0.003978383705929  
 $Y_{21}$  -0.003978307748375  
 $Y_{22}$  0.045992716542651



# Curve Fitting Results of Y-Parameters



# FDTD Results of the Bandpass Filter



FDTD simulated results with inverse Laplace transform vs. measured results.

# Poles and Residues of a Lowpass Filter with XFDTD Simulated S-Parameters

## Y<sub>11</sub> Residues

31812050.288548764000  
 -67720.378185156267  
 (37529822.648174129000,-40026.932531441707)  
 (-175537.295868410210,100652.444307371570)  
 (32392712.101842962000,-14512.622772633333)  
 (6270545.547076162000,-207580.103401408180)  
 (49156211.928048506000,2050072.390816211700)  
 (129731961.875055690000,460418.940590875340)

## Y<sub>21</sub> Residues

-31812468.753139541000  
 75753.944933024948  
 (39457704.640739337000,-39201.331262409738)  
 (217020.159751129800,-38824.076965930770)  
 (-26321027.264643978000,-9834.522905352111)  
 (21515279.215645216000,-80330.984723144895)  
 (-25415085.211731233000,338694.722983689340)  
 (12642396.875211176000,-2714517.396533716900)

## Poles

-975499.326105132930  
 -182376301.994609360000  
 (-768821.177385819610,5213972461.037248600000)  
 (-1998672141.173676500000,6844683932.097068800000)  
 (-19353320.144730210000,7689094515.626965500000)  
 (-17228320.405101445000,19450970805.905277000000)  
 (-16142328.993978474000,21311629765.987656000000)  
 (-11653615720.134962000000,32355121510.571266000000)

## Y<sub>12</sub> Residues

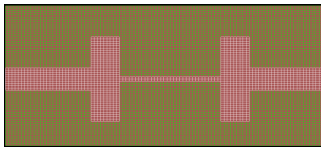
-31813592.799060587000  
 78301.228427462629  
 (39457266.054141641000,-45556.762022539915)  
 (211703.907292048940,-24848.565070452780)  
 (-26311467.861838698000,-17154.272250205446)  
 (21400107.453707609000,-202104.424720217970)  
 (-25041759.577760383000,416622.199634957070)  
 (12059010.913733162000,-2200955.706581799300)

## Y<sub>22</sub> Residues

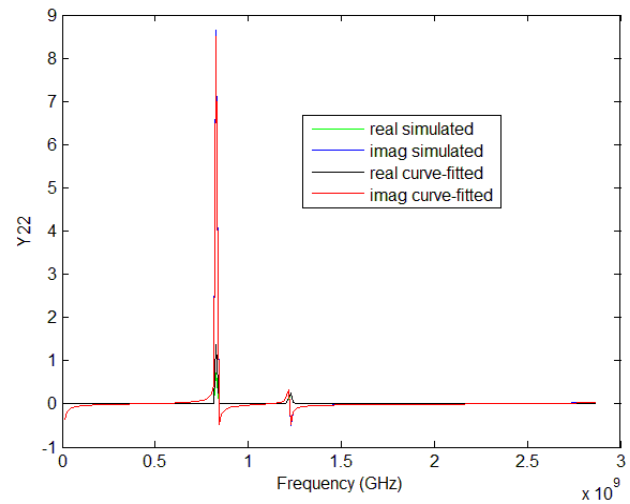
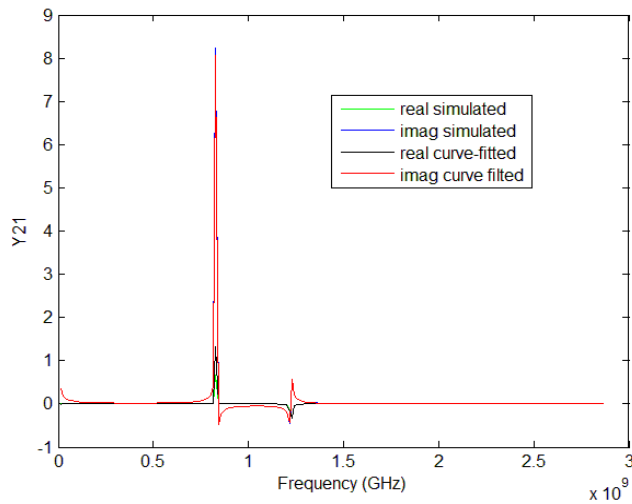
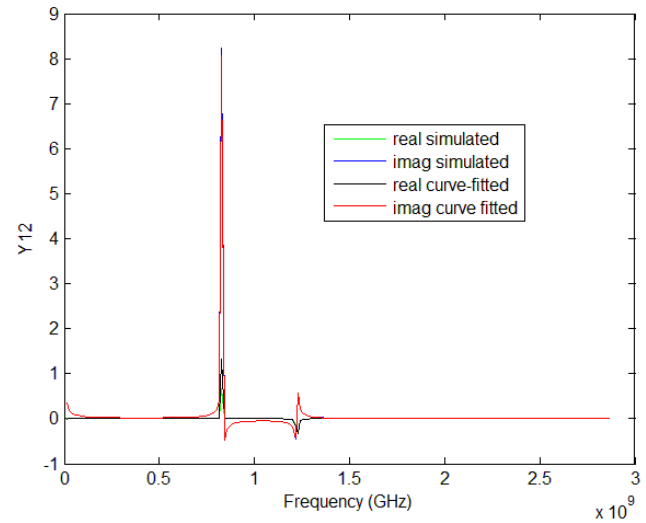
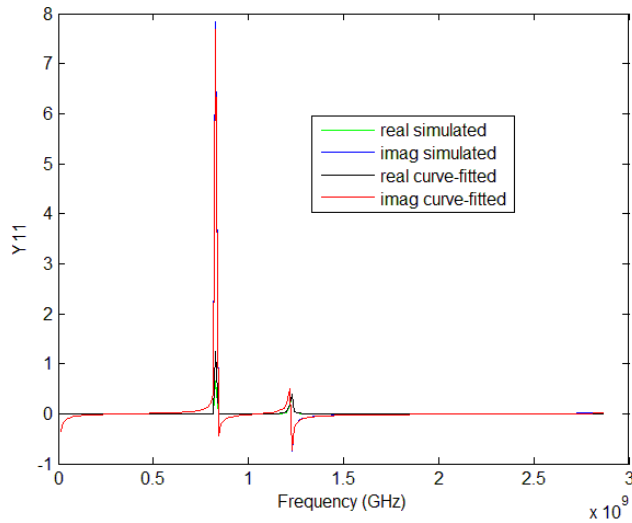
31812588.873190239000  
 -82279.456605251486  
 (41485349.264375225000,-43913.246282403590)  
 (-119752.664515433000,84499.041433761216)  
 (21376426.643237699000,31852.822150754459)  
 (55805643.720411658000,-396771.982839323350)  
 (17001996.008426346000,1789434.263083778800)  
 (106321194.371849310000,1608058.822462805100)

## α

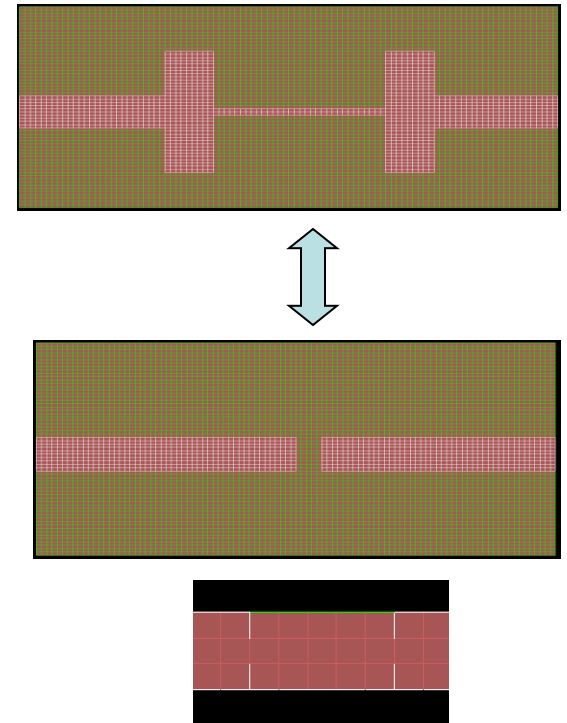
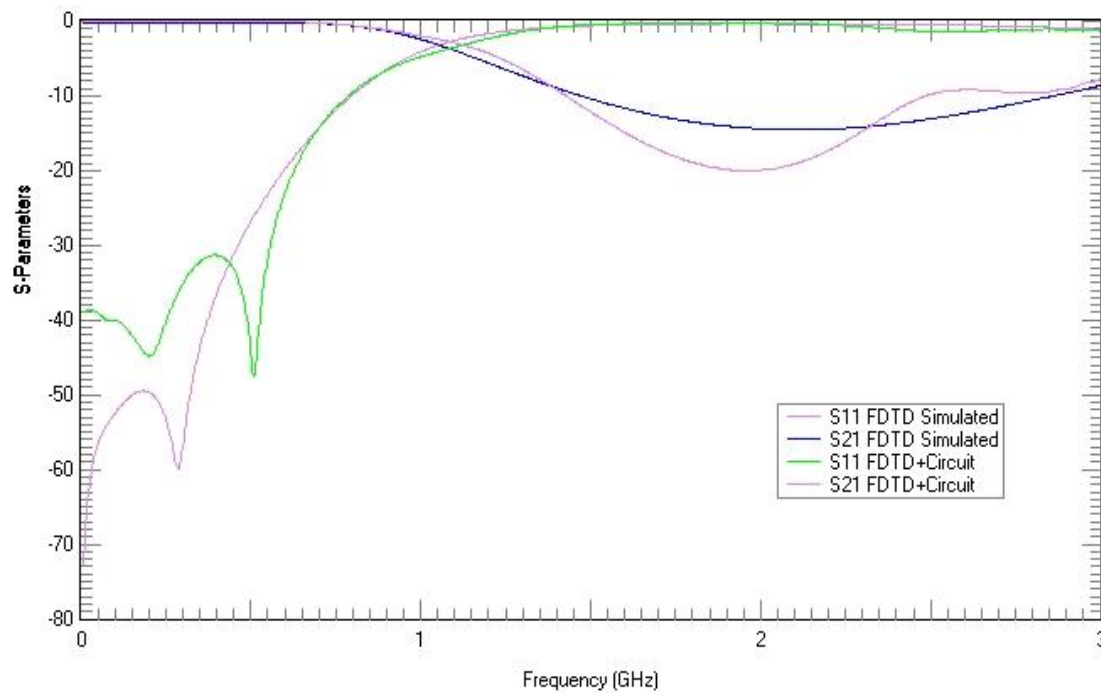
Y<sub>11</sub> -0.000006146043415  
 Y<sub>12</sub> -0.000041757518324  
 Y<sub>21</sub> -0.000064686896071  
 Y<sub>22</sub> 0.000247556357697



# Curve Fitting Results of Y-Parameters

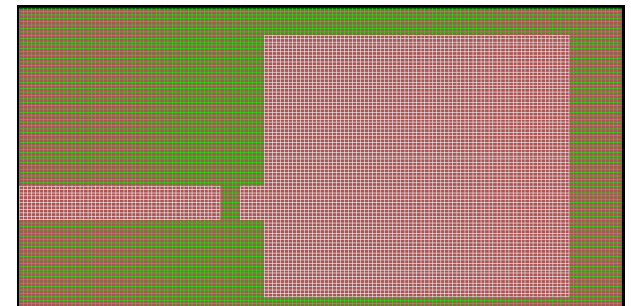
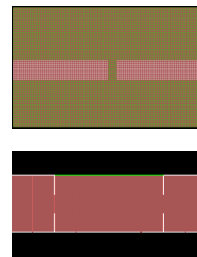
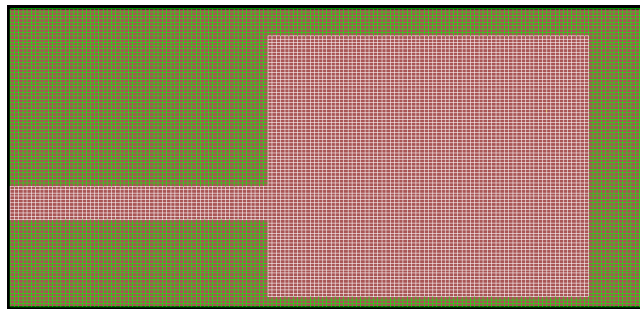
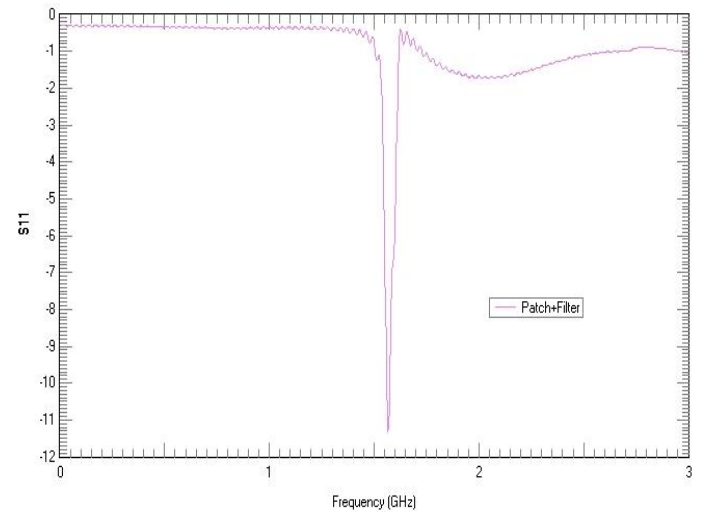
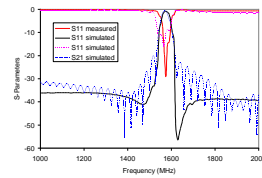
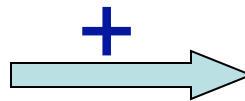
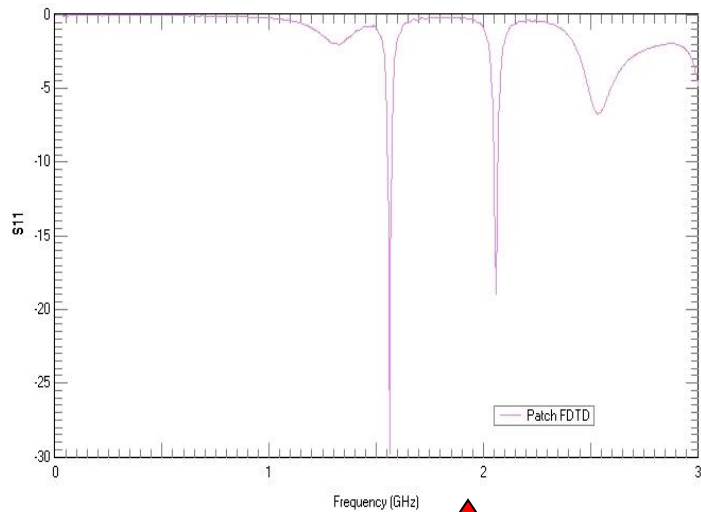


# Simulated S-Parameters of the Lowpass Filter



FDTD simulated results using a circuit network vs. the LPF geometry.

# Patch Antenna + Bandpass Filter



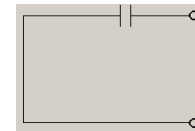
# Discussion (1): Admittance

- Additional term for admittance  $Y$

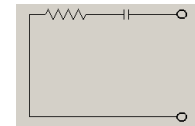
$$Y(s) \approx \sum_{i=1}^M \frac{r_i}{s - p_i} + \alpha + sh$$

Chen and Chu, *Progress In Electromagnetics Research*, PIER vol.73, pp.327–341, 2007 (piecewise linear recursive convolution).

➤ Pure C or Shunt C:  $Y=sC$



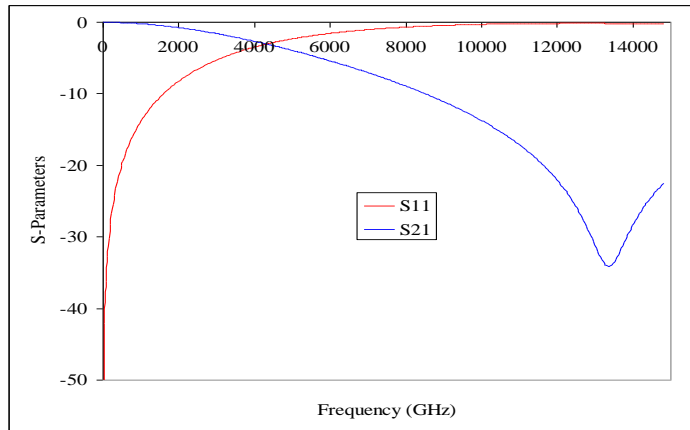
➤ Series RC:  $Y=sC/(1+sRC)$



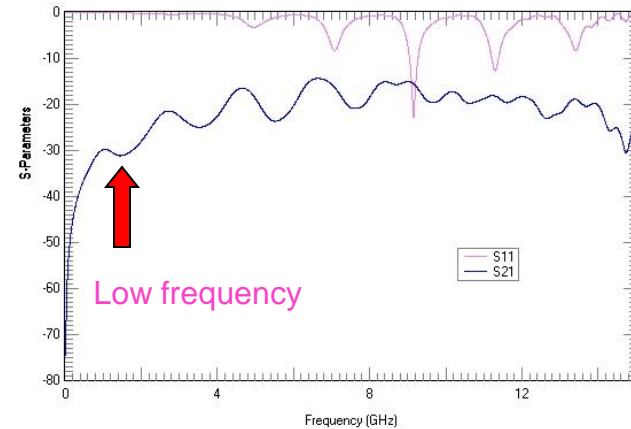
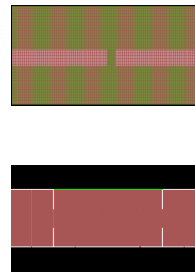
- From poles/residues to rational functions

$$Y(s) \approx \sum_{i=1}^M \frac{r_i}{s - p_i} + \alpha \quad \longrightarrow \quad Y_{pq}(s) = \frac{\sum_{m=0}^{M_{pq}} a_m^{(p,q)} s^m}{\sum_{n=0}^{N_{p,q}} b_n^{(p,q)} s^n}$$

# Discussion (2): Chip Inductor



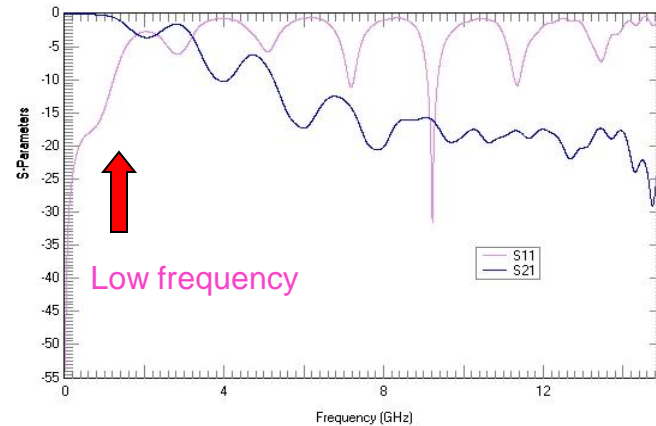
Measured S-parameters of a chip inductor (~3nH)



S-parameters of a microstrip gap

Extracted two Poles and residues from  $Y_{11}$  of the chip inductor

**Poles**  
 -338390130769.24915000000  
 -4574092.101910794200  
**Residues**  
 -4934782755.19058800000  
 302889269.765195730000  
 $\alpha$   
 0.014614553416800

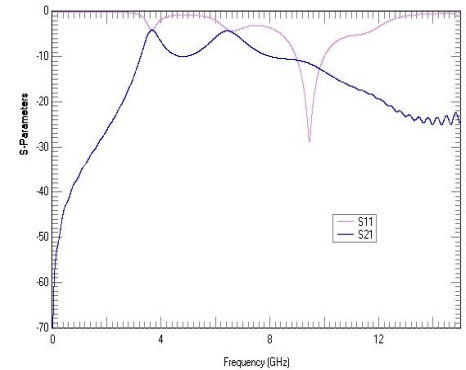
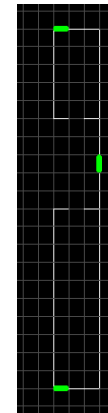
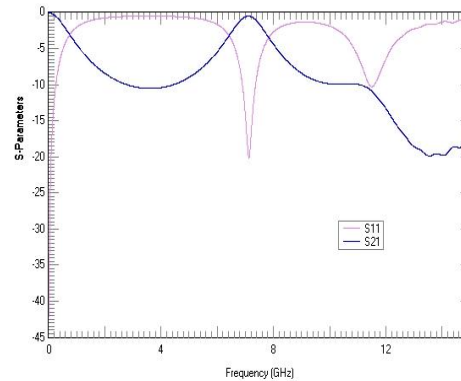
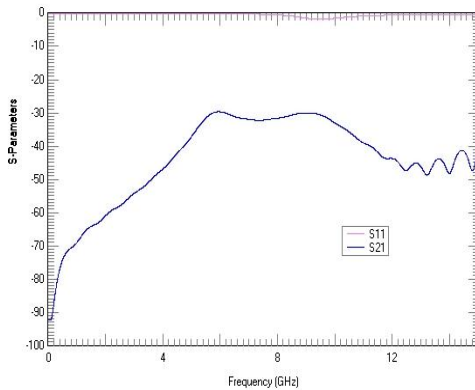
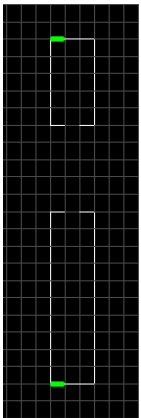
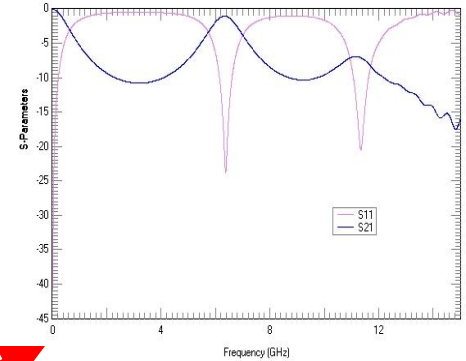
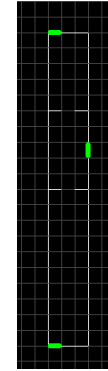
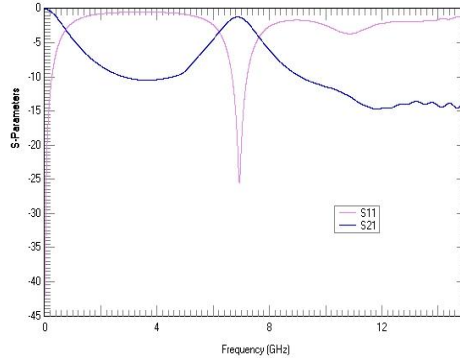
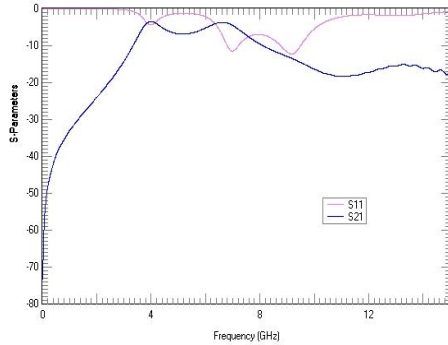
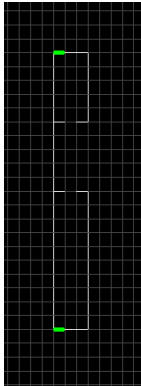


Simulated S-parameters of a chip inductor (2 poles)

Effect of microstrip transmission line on S-parameters



# Discussion (3): Wire Connector

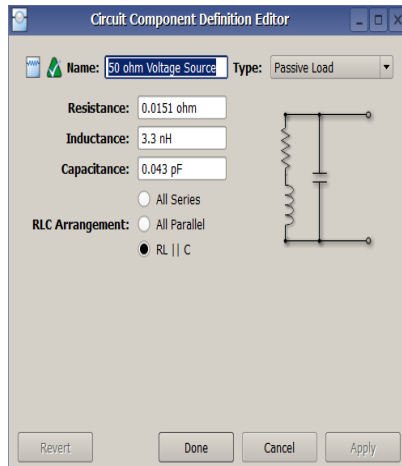


S-parameters for connected or broken ground wires

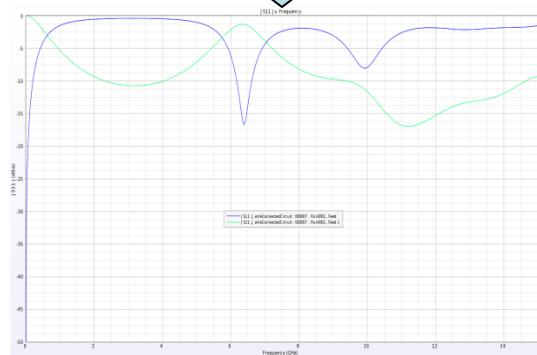
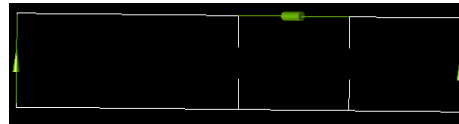
S-parameters for a chip inductor with connected or broken ground wires

S-parameters for a 3 nH inductor as a lumped element

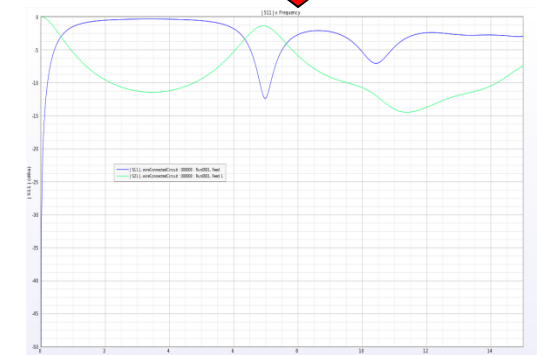
# Discussion (4): Equivalent Circuit



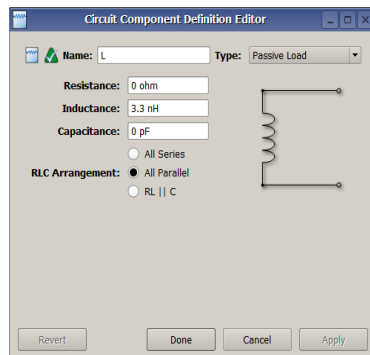
Equivalent circuit of a chip inductor  
(Circuit parameters are obtained by PSO)



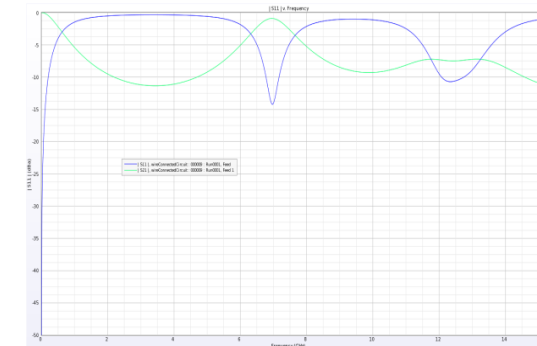
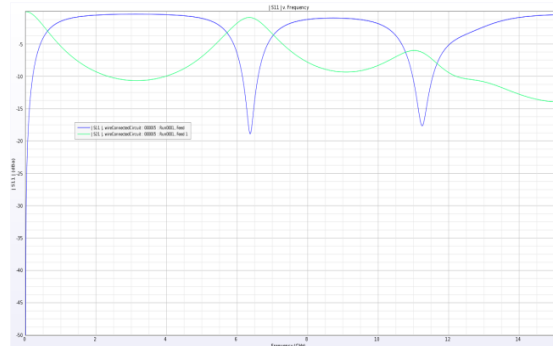
S-parameters of the equivalent circuit of chip inductor



S-parameters of 3.3 nH pure inductor



Pure inductor



Effect of connecting wires on S-parameters

# Conclusion

- Electronic devices characterized by simulated and measured S-parameters can be simulated in FDTD using the inverse Laplace transform combined with the passivity enforcement method.
- The simulation is quite accurate and robust once the admittance is well represented by poles and residues.
- The effects of microstrip and wires connecting the circuit network cannot be ignored.
- This combined FDTD and circuit method can be applied to simulate geometries together with these devices characterized by simulated and measured S-parameters.



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